

Weihua Wu

List of Publications by Year in descending order

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27
papers

358
citations

840776

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docs citations

27
times ranked

185
citing authors

#	ARTICLE	IF	CITATIONS
1	Ge ₂ Sb ₂ Te ₅ /Sb superlattice-like thin film for high speed phase change memory application. Applied Physics Letters, 2015, 107, .	3.3	57
2	Crystallization characteristic and scaling behavior of germanium antimony thin films for phase change memory. Nanoscale, 2018, 10, 7228-7237.	5.6	33
3	Understanding the crystallization behavior and structure of titanium addition in germanium antimony phase change thin films. Journal of Materials Chemistry C, 2018, 6, 9081-9092.	5.5	28
4	Improvement of the thermal stability of Sb thin film through erbium doping. CrystEngComm, 2016, 18, 6365-6369.	2.6	26
5	Ti _x Sb _{100-<i>x</i>} thin films as candidates for phase-change memory application. Applied Physics Letters, 2017, 110, .	3.3	25
6	Multi-level storage and ultra-high speed of superlattice-like Ge ₅₀ Te ₅₀ /Ge ₈ Sb ₉₂ thin film for phase-change memory application. Nanotechnology, 2017, 28, 405206.	2.6	22
7	Study on the physical properties and structure of titanium antimony thin films for phase change memory application. Journal of Materials Science, 2017, 52, 11598-11607.	3.7	21
8	Investigation on the crystallization properties and structure of oxygen-doped Ge ₈ Sb ₉₂ phase change thin films. Journal Physics D: Applied Physics, 2017, 50, 095602.	2.8	20
9	High speed and low power consumption of superlattice-like Ge/Sb ₇₀ Se ₃₀ thin films for phase change memory application. Journal of Materials Science: Materials in Electronics, 2016, 27, 2183-2188.	2.2	14
10	Improvement of the thermal stability and power consumption of Sb ₇₀ Se ₃₀ through nitrogen doping. Journal of Materials Science: Materials in Electronics, 2015, 26, 9700-9706.	2.2	12
11	Physical properties and structure characteristics of titanium-modified antimony-selenium phase change thin film. Applied Physics Letters, 2021, 118, .	3.3	12
12	N-doped Zn ₁₅ Sb ₈₅ phase-change materials for higher thermal stability and lower power consumption. Journal of Materials Science: Materials in Electronics, 2014, 25, 2943-2947.	2.2	11
13	Superlattice-like Sb-Ge thin films for high thermal stability and low power phase change memory. Journal of Alloys and Compounds, 2018, 738, 145-150.	5.5	11
14	<i>In-situ</i> investigation on the crystallization property and microstructure evolution induced by thermal annealing and electron beam irradiation of titanium antimony thin film. Applied Physics Letters, 2019, 115, .	3.3	11
15	Al _x (Sn ₂ Se ₃) _{1-<i>x</i>} phase change films for high-temperature data retention and fast transition speed application. Journal of Materials Science: Materials in Electronics, 2015, 26, 7757-7762.	2.2	9
16	Superlattice-like Ga ₄₀ Sb ₆₀ /Sb films with ultra-high speed and low power for phase change memory application. Journal of Materials Science: Materials in Electronics, 2017, 28, 3806-3811.	2.2	9
17	Investigation of multilayer SnSb ₄ /ZnSb thin films for phase change memory applications. Applied Physics Express, 2017, 10, 055504.	2.4	8
18	Fast switching and low power of superlattice-like SnSe ₂ /Sb thin films for phase change memory application. Journal of Applied Physics, 2016, 120, 165106.	2.5	6

#	ARTICLE	IF	CITATIONS
19	Performance Improvement of Sb Phase Change Thin Film by Y Doping. ECS Journal of Solid State Science and Technology, 2021, 10, 093002.	1.8	6
20	The optimization effect of titanium on the phase change properties of SnSb ₄ thin films for phase change memory applications. CrystEngComm, 2020, 22, 5002-5009.	2.6	4
21	Uncovering the physical properties, structural characteristics, and electronic application of superlattice-like Ti/Sb phase-change thin films. Journal Physics D: Applied Physics, 2022, 55, 245102.	2.8	3
22	Crystallization properties and structural evolution of amorphous Ti-doped Sn ₂₀ Sb ₈₀ thin layers induced by heating and irradiating. Journal of Applied Physics, 2022, 131, .	2.5	3
23	Sb ₇ Te ₃ /Ge multilayer films for low power and high speed phase-change memory. Semiconductor Science and Technology, 2017, 32, 065003.	2.0	2
24	Impact of atomic vacancy on phase change and structure in Ge _x Te _{1-x} films. Journal of Materials Science: Materials in Electronics, 2020, 31, 5936-5940.	2.2	2
25	Thickness effect on the crystallization characteristic of RF sputtered Sb thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 24240-24247.	2.2	2
26	Accurate Phase Change Behavior Characterization Of Ultrathin Sb-Rich Films Based On Superlattice-like Al/Ge ₁₀ Sb ₉₀ System. Journal of Electronic Materials, 2022, 51, 190.	2.2	1
27	Investigation of crystallization behavior and structure of nanocomposite multilayer phase change thin films with zinc antimony and germanium antimony. Journal Physics D: Applied Physics, 2020, 53, 135106.	2.8	0